NPN Epitaxial Silicon Transistor
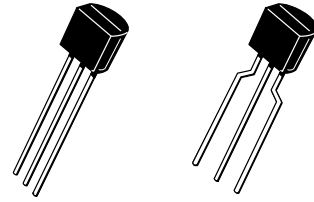
KSP10

Features

- VHF/UHF Transistor
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
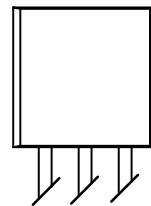
ABSOLUTE MAXIMUM RATINGS

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CBO}	Collector Base Voltage	30	V
V_{CEO}	Collector Emitter Voltage	25	V
V_{EBO}	Emitter Base Voltage	3.0	V
PC	Collector Power Dissipation (T_A = 25°C)	350	mW
	Derate above 25°C	2.8	mW/°C
PC	Collector Power Dissipation (T_C = 25°C)	1.0	W
	Derate above 25°C	8.0	W/°C
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	55 to 150	°C
Rth(j c)	Thermal Resistance, Junction to Case	125	°C/W
Rth(j a)	Thermal Resistance, Junction to Ambient	357	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

TO–92–3
CASE 135AN

TO–92 LF
CASE 135AR

1:Base
2:Emitter
3:Collector

MARKING DIAGRAM

AKS
P10
YWW

A = Assembly Code
KSP10 = Device Code
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
KSP10BU	TO 92 3 (Pb Free)	10000 / Bulk Bag
KSP10TA	TO 92 3 LF (Pb Free)	2000 / Fan Fold

Publication Order Number:
KS910/D

KSP10

ELECTRICAL CHARACTERISTICS (Values are at $T_A = 25°C$ unless otherwise noted.)

Symbol	Parameter	Conditions	Min	Max	Unit
BV_{CBO}	Collector Base Breakdown Voltage	$I_C = 100 \ \mu A, I_E = 0$	30		

TYPICAL CHARACTERISTICS (CONTINUED)

TO−92 3 4.825x4.76
CASE 135AN
ISSUE O

DATE 31 JUL 2016

5.20
4.32

5.3⁷
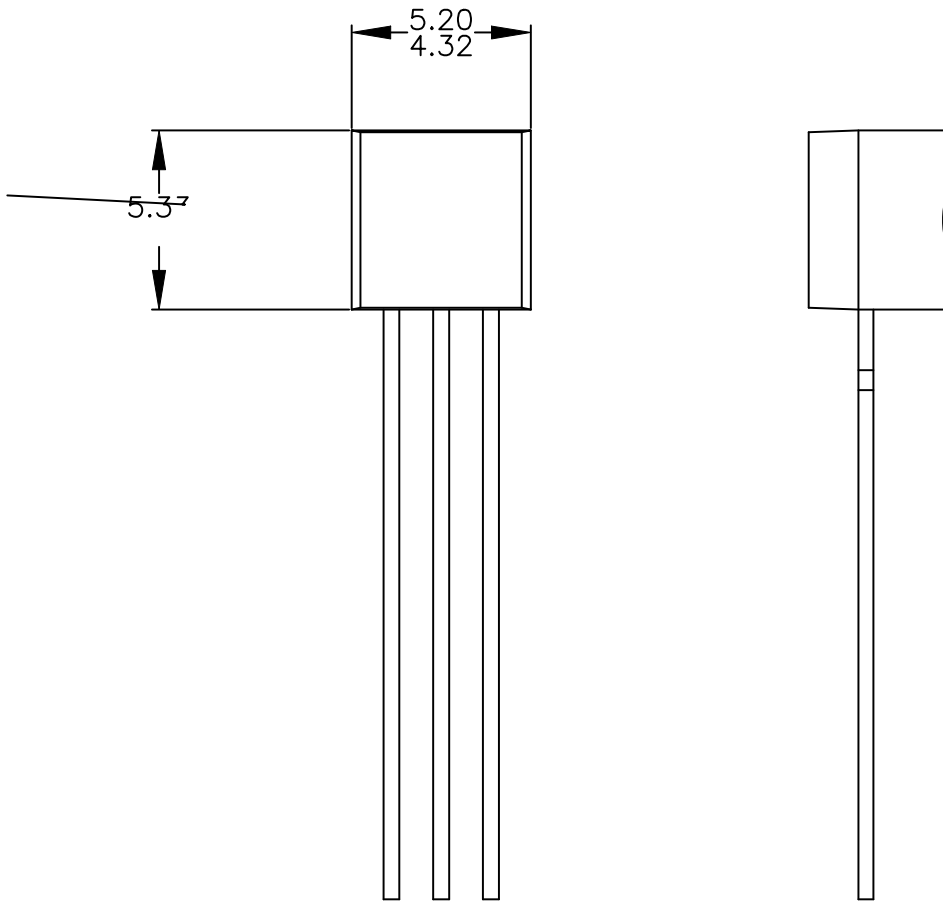
TO–92 3 4.83x4.76 LEADFORMED
CASE 135AR
ISSUE O

DATE 30 SEP 2016